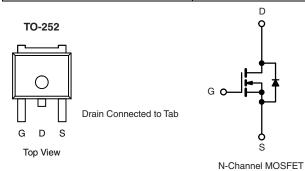


Automotive N-Channel 40 V (D-S) 175 °C MOSFET

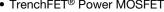
PRODUCT SUMMARY				
V _{DS} (V)	40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.010			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.014			
I _D (A)	42			
Configuration	Single			



FEATURES

• Halogen-free According to IEC 61249-2-21 **Definition**





- Package with Low Thermal Resistance
- 100 % R_q and UIS Tested
- AEC-Q101 Qualifieddd
- Compliant to RoHS Directive 2002/95/EC



ORDERING INFORMATION			
Package	TO-252		
Lead (Pb)-free and Halogen-free	SQD40N04-10A-GE3		

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	40		
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current ^a	T _C = 25 °C	1	42		
	T _C = 125 °C	- I _D	35		
Continuous Source Current (Diode Conduction) ^a		I _S	42	Α	
Pulsed Drain Current ^b		I _{DM}	168		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	30		
Single Pulse Avalanche Energy	L=0.11IIIA	E _{AS}	45	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	D	71	\\\\	
	T _C = 125 °C	P_{D}	24	W	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	50	°C/W
Junction-to-Case (Drain)		R _{thJC}	2.1	G/VV

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



Automotive N-Channel 40 V (D-S) 175 ??C MOSFET

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static	1			L	L	L		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		40	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$		2.0	2.5	7 V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 40 V	=.	-	1.0		
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μA	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	150		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	50	-	-	Α	
		V _{GS} = 10 V	I _D = 20 A	=.	0.006	0.010		
Drain Cauras On State Resistance	В	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	=.	-	0.016		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.019	Ω	
		V _{GS} = 4.5 V	I _D = 20 A	-	0.011	0.014	1	
Forward Transconductanceb	9 _{fs}	V _{DS} = 15 V, I _D = 40 A		-	58	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			=.	1755	2190		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	=.	385	480	pF	
Reverse Transfer Capacitance	C _{rss}]		=.	250	315		
Total Gate Charge ^c	Qg			-	46	70		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 20 \text{ V}, I_D = 40 \text{ A}$	-	6.2	-	nC	
Gate-Drain Charge ^c	Q _{gd}]		=.	13.5	-		
Gate Resistance	R _g	f = 1 MHz		1.1	2.2	3.3	Ω	
Turn-On Delay Time ^c	t _{d(on)}				7	10		
Rise Time ^c	t _r	$V_{DD} = 20 \text{ V}, R_L = 0.5 \Omega$ $I_D \cong 40 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		-	10	15	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	25	37		
Fall Time ^c	t _f			-	9	14		
Source-Drain Diode Ratings and Char	acteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	168	Α	
Forward Voltage	V _{SD}	I _F = 40 A, V _{GS} = 0 V		-	0.8	1.2	V	

Notes

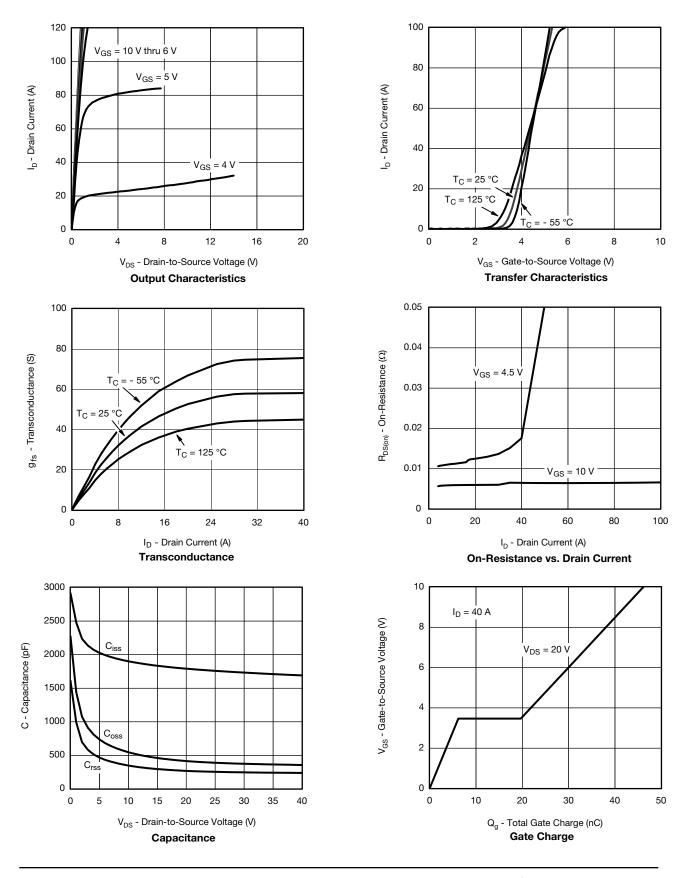
- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



Automotive N-Channel 40 V (D-S) 175 ??C MOSFET

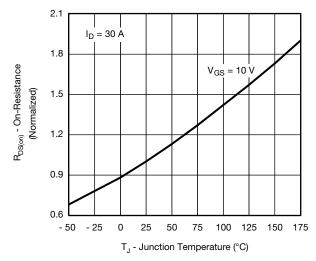
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



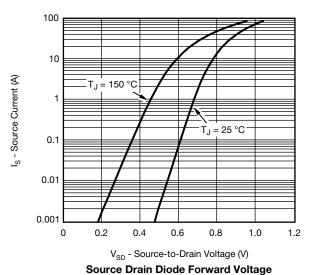


Automotive N-Channel 40 V (D-S) 175 ??C MOSFET

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

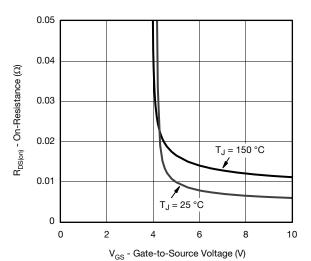


On-Resistance vs. Junction Temperature

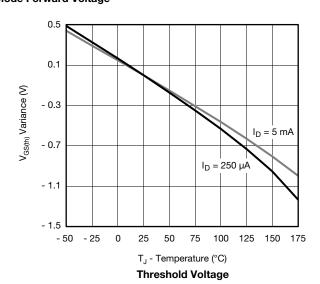


I_D = 10 mA V_{DS} - Drain-to-Source Voltage (V) 52 49 46 43 40 - 25 125 150 175 - 50 0 25 50 75 100 T_J - Junction Temperature (°C)

Drain Source Breakdown vs. Junction Temperature

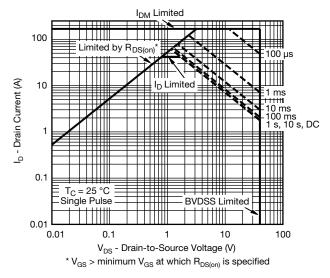


On-Resistance vs. Gate-to-Source Voltage

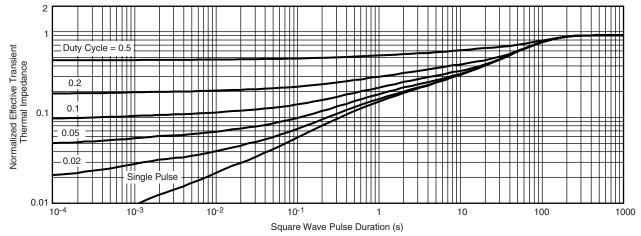


Automotive N-Channel 40 V (D-S) 175 ??C MOSFET

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



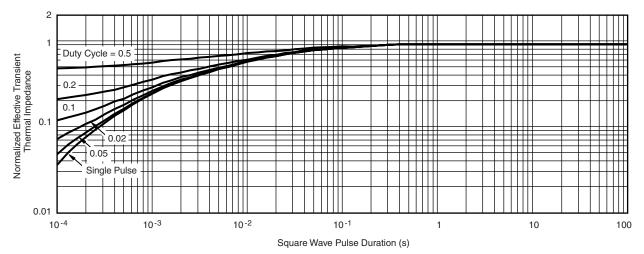
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

Automotive N-Channel 40 V (D-S) 175 ??C MOSFET

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

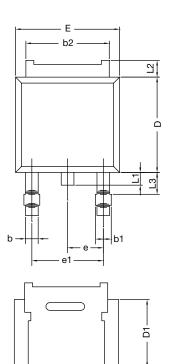
Note

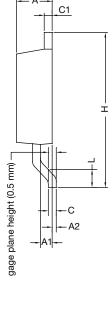
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



Automotive N-Channel 40 V (D-S) 175 ??C MOSFET

TO-252AA CASE OUTLINE





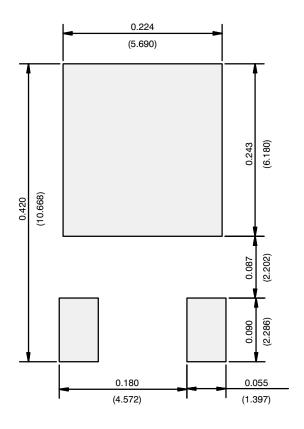
	MILLIN	IETERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
Е	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28	BSC	0.090 BSC		
e1	4.57 BSC		0.180 BSC		
т	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

Note

• Dimension L3 is for reference only.

Automotive N-Channel 40 V (D-S) 175 ??C MOSFET

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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Automotive N-Channel 40 V (D-S) 175 ??C MOSFET

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